
6AM13

Silicon N-Channel/P-Channel Complementary Power MOS FET
Array

HITACHI

ADE-208-1217 (Z)
1st. Edition
Mar. 2001

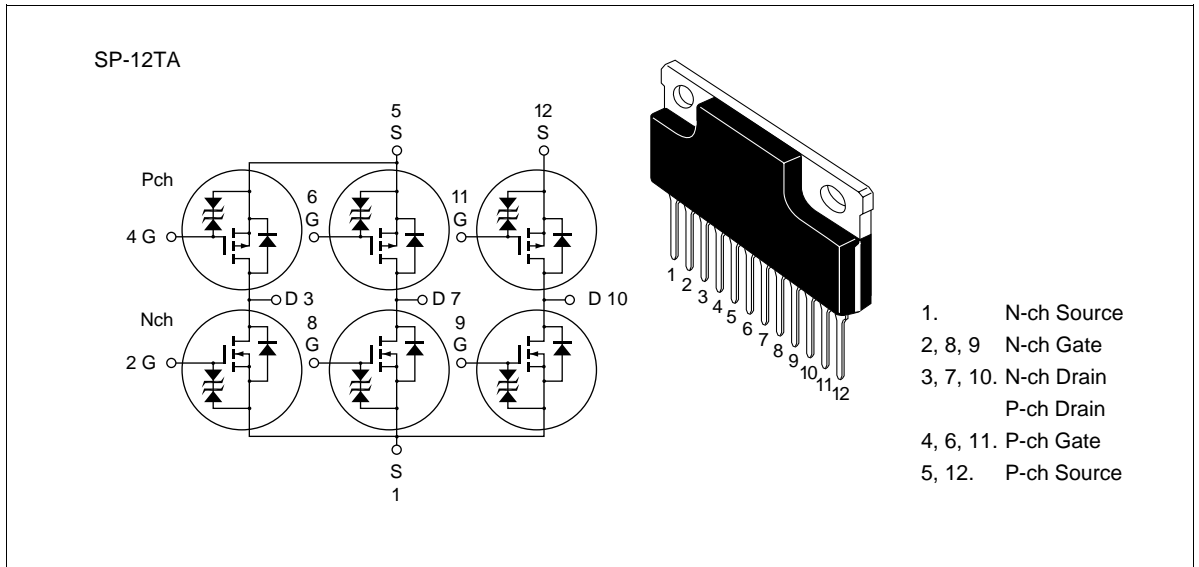
Application

High speed power switching

Features

- Low on-resistance
N-channel: $R_{DS(on)} \leq 0.075$, $V_{GS} = 10$ V, $I_D = 5$ A
P-channel: $R_{DS(on)} \leq 0.12$, $V_{GS} = -10$ V, $I_D = -5$ A
- Capable of 4 V gate drive
- Low drive current
- High speed switching
- High density mounting
- Suitable for H-bridged motor driver

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		
		Nch	Pch	Unit
Drain to source voltage	V_{DSS}	60	-60	V
Gate to source voltage	V_{GSS}	±20	±20	V
Drain current	I_D	10	-10	A
Drain peak current	$I_{D(pulse)}^{*1}$	40	-40	A
Body to drain diode reverse drain current	I_{DR}	10	-10	A
Channel dissipation	Pch (Tc = 25°C) ^{*2}	42		W
Channel dissipation	Pch ^{*2}	4.8		W
Channel temperature	Tch	150		°C
Storage temperature	Tstg	-55 to +150		°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. 6 devices operation

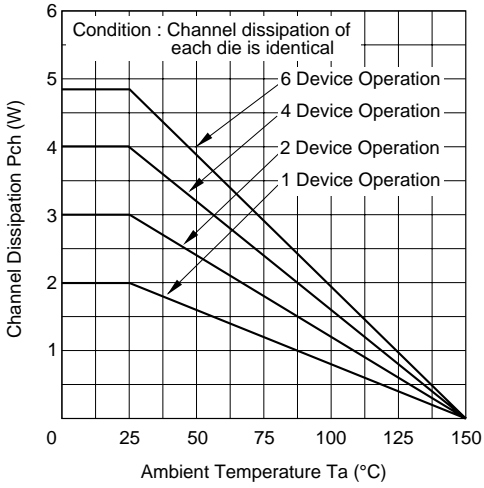
Electrical Characteristics (Ta = 25°C) (1 Unit)

Item	Symbol	N channel			P channel			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	-60	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	—	—	-250	μA	$V_{DS} = 50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	-1.0	—	-2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.06	0.075	—	0.09	0.12	Ω	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
		—	0.08	0.11	—	0.12	0.18	Ω	$I_D = 5 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	6	9.5	—	5	8	—	S	$I_D = 5 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	860	—	—	1400	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	450	—	—	720	—	pF	
Reverse transfer capacitance	C_{rss}	—	140	—	—	220	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	—	15	—	ns	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V},$ $R_L = 6 \text{ }\Omega$
Rise time	t_r	—	50	—	—	100	—	ns	
Turn-off delay time	$t_{d(off)}$	—	180	—	—	250	—	ns	ns
Fall time	t_f	—	110	—	—	160	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	—	-1.0	—	V	$I_F = 10 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	120	—	—	200	—	ns	$I_F = 10 \text{ A}, V_{GS} = 0,$ $diF/dt = 50 \text{ A}/\mu\text{s}$

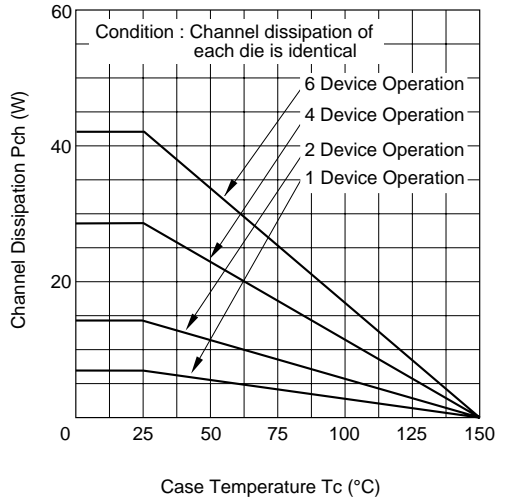
Note: 1. Pulse Test

Polarity of test conditions for P channel device is reversed.

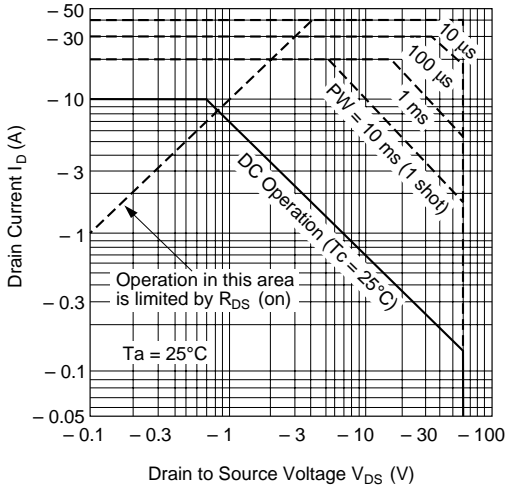
Maximum Channel Dissipation Curve



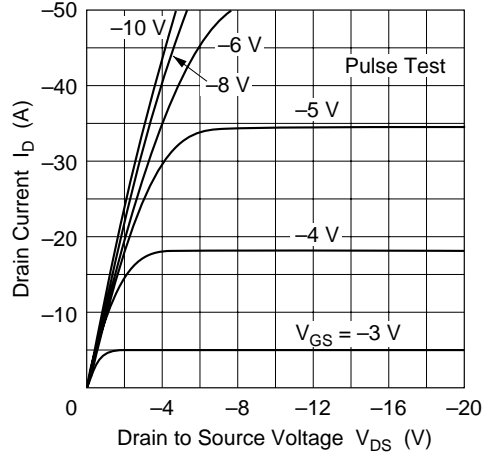
Maximum Channel Dissipation Curve

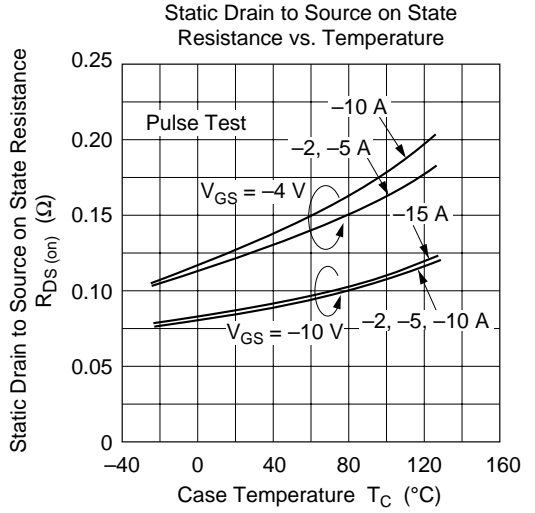
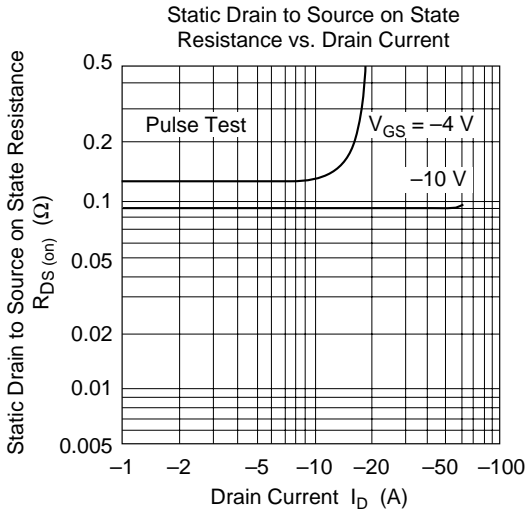
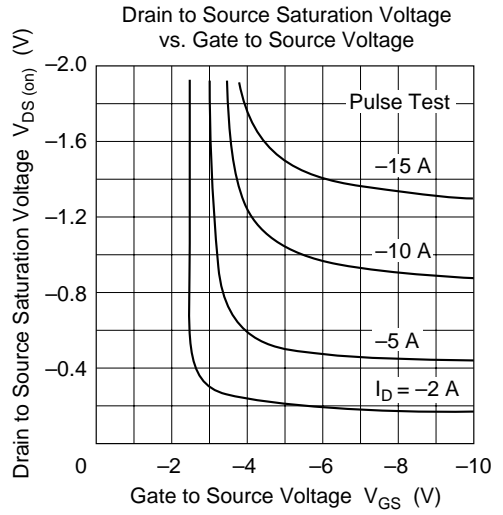
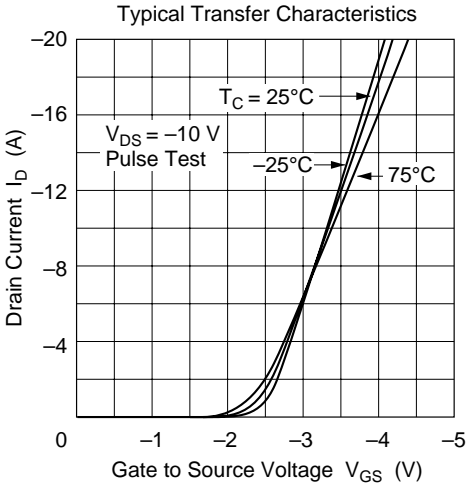


Maximum Safe Operation Area (P-Channel)

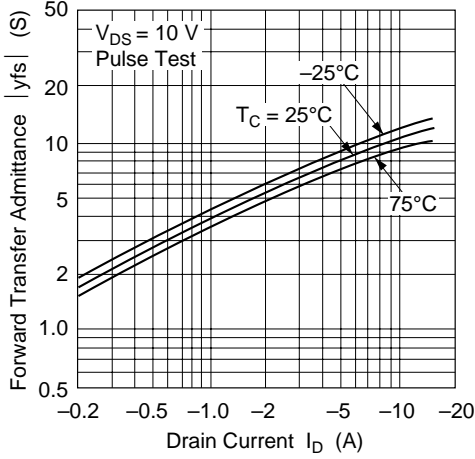


Typical Output Characteristics

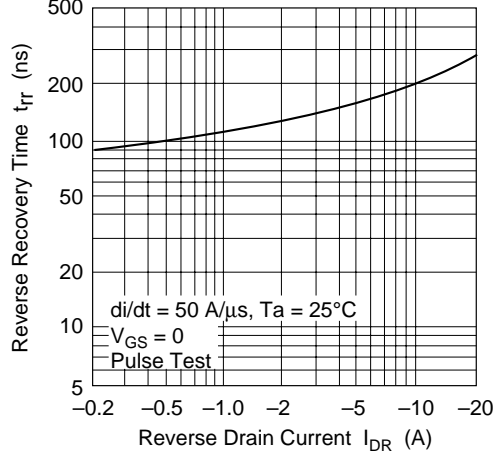




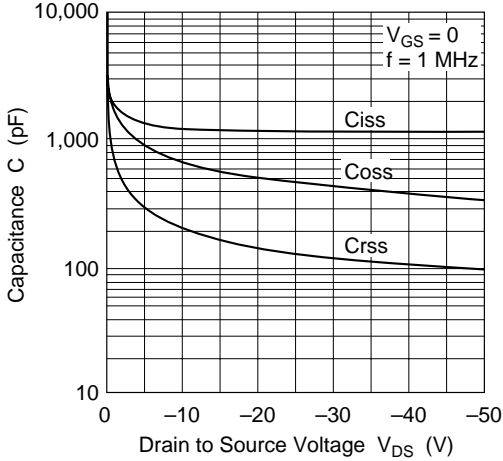
Forward Transfer Admittance vs. Drain Current



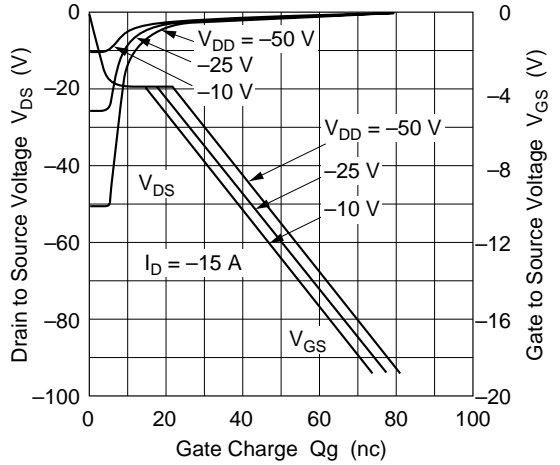
Body to Drain Diode Reverse Recovery Time



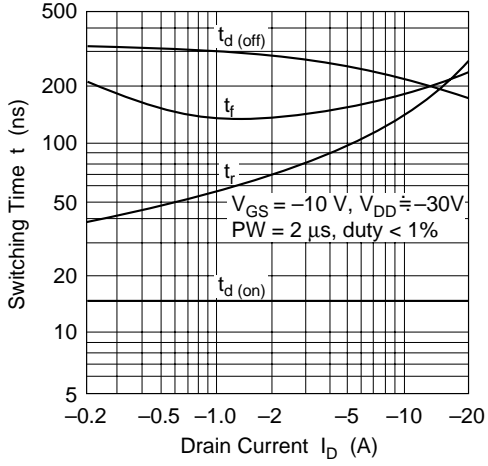
Typical Capacitance vs. Drain to Source Voltage



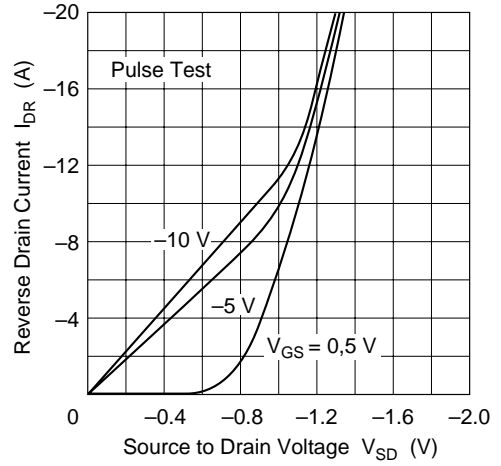
Dynamic Input Characteristics



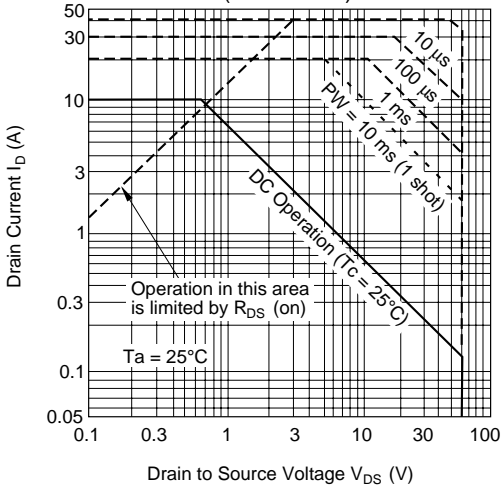
Switching Characteristics



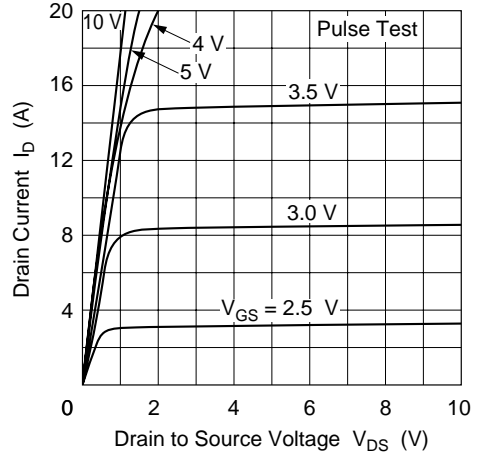
Reverse Drain Current vs. Source to Drain Voltage



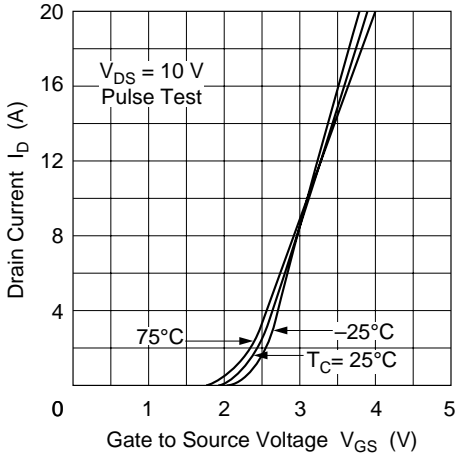
Maximum Safe Operation Area (N-Channel)



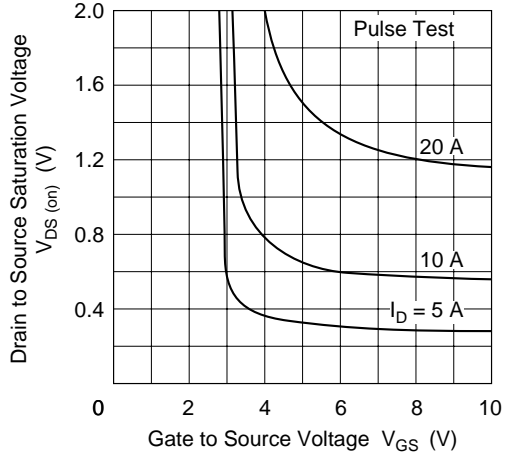
Typical Output Characteristics

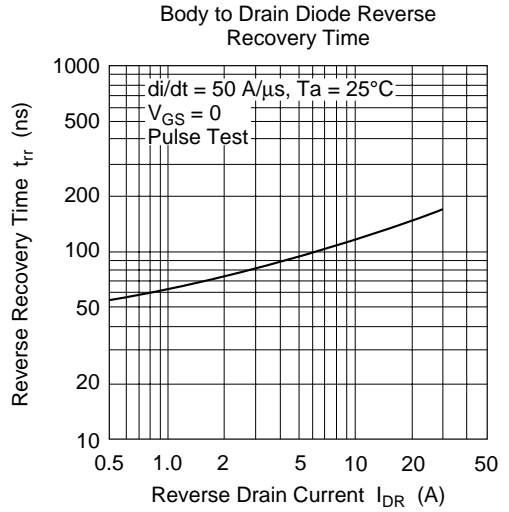
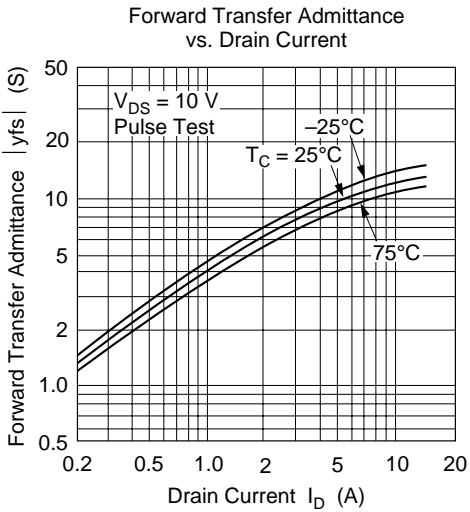
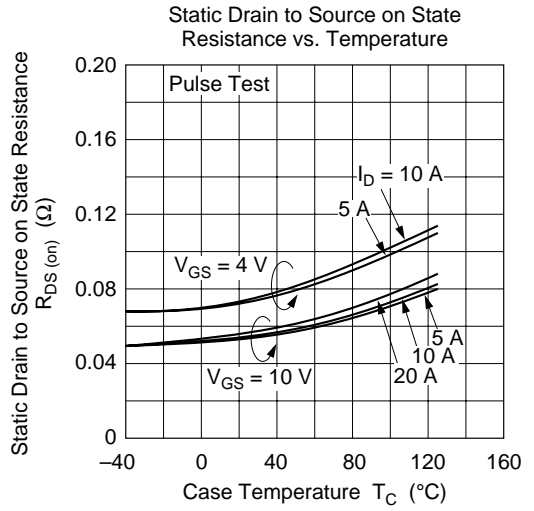
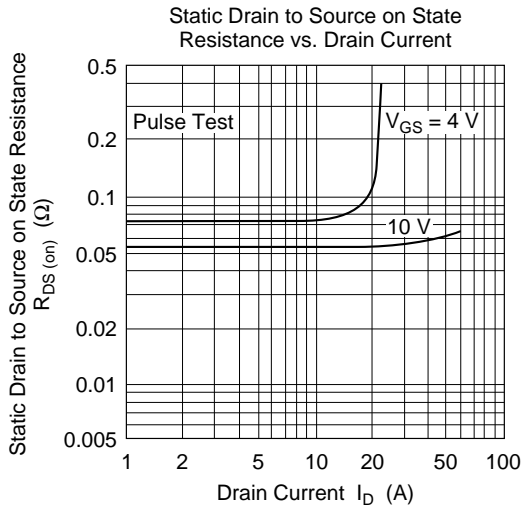


Typical Transfer Characteristics

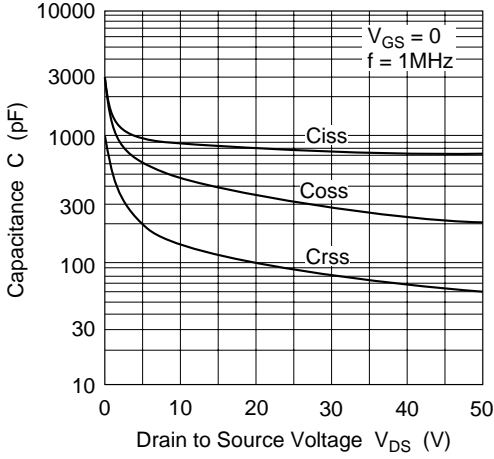


Drain to Source Saturation Voltage vs. Gate to Source Voltage

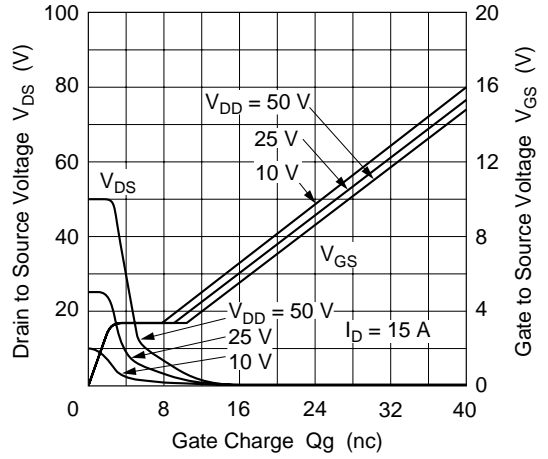




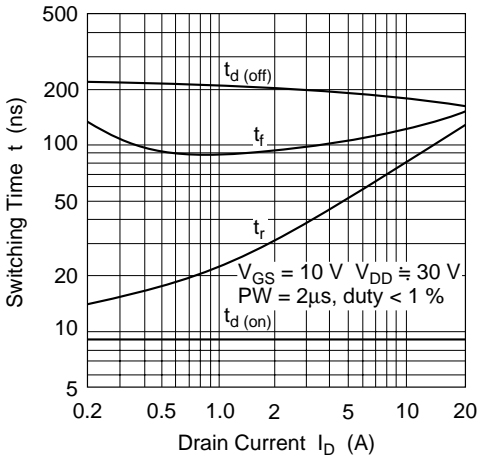
Typical Capacitance vs. Drain to Source Voltage



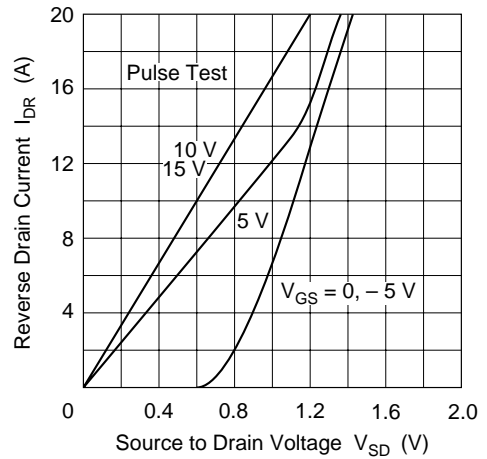
Dynamic Input Characteristics



Switching Characteristics

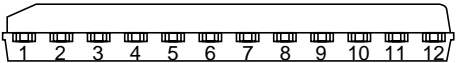
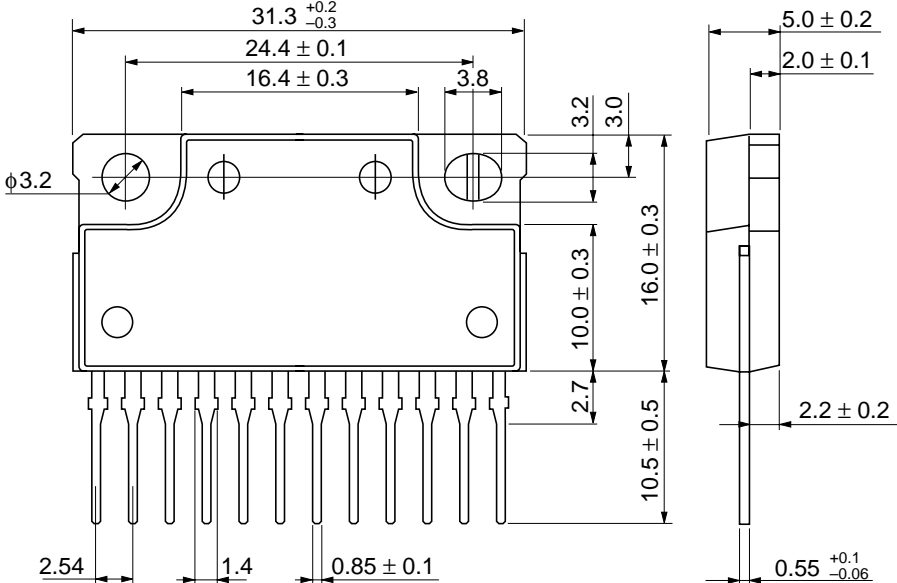
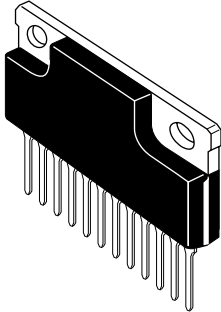


Reverse Drain Current vs. Source to Drain Voltage



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	SP-12TA
JEDEC	—
EIAJ	—
Mass (reference value)	6.1 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive,
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen, Munich
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
 Electronic Components Group.
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00,
 Singapore 049318
 Tel: <65>-538-6533/538-8577
 Fax: <65>-538-6933/538-3877
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Hitachi Asia Ltd.
 (Taipei Branch Office)
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 Hung-Kuo Building,
 Taipei (105), Taiwan
 Tel: <886>-(2)-2718-3666
 Fax: <886>-(2)-2718-8180
 Telex: 23222 HAS-TP
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Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower,
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon,
 Hong Kong
 Tel: <852>-(2)-735-9218
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